

*New Jersey Semi-Conductor Products, Inc.*

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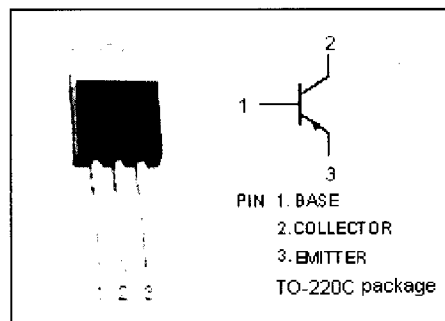
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## Silicon PNP Power Transistor

## 2SA1262

### DESCRIPTION

- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = -60V(\text{Min.})$
- Low Collector Saturation Voltage  
:  $V_{CE(sat)} = -0.6V(\text{Max.})@I_C = -2A$
- Complement to Type 2SC3179

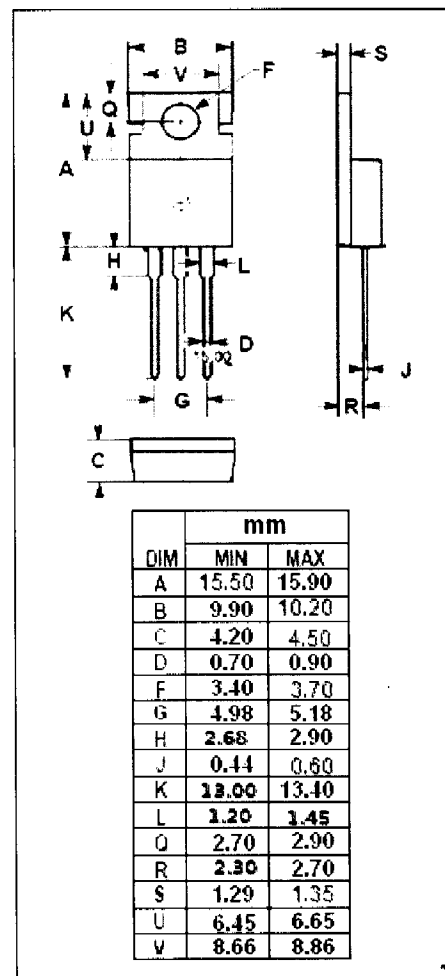


### APPLICATIONS

- Designed for audio and general purpose applications.

### ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-60	V
$V_{CEO}$	Collector-Emitter Voltage	-60	V
$V_{EBO}$	Emitter-Base Voltage	-6	V
$I_C$	Collector Current-Continuous	-4	A
$I_B$	Base Current-Peak	-1	A
$P_C$	Total Power Dissipation @ $T_c=25^\circ\text{C}$	30	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

**Quality Semi-Conductors**

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## ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -25\text{mA}; I_B = 0$	-60			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -2\text{A}; I_B = -0.2\text{A}$			-0.6	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -60\text{V}; I_E = 0$			-100	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -6\text{V}; I_C = 0$			-100	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -4\text{V}$	40			
$f_T$	Current-Gain—Bandwidth Product	$I_E = 0.2\text{A}; V_{CE} = -12\text{V}$		15		MHz
$C_{OB}$	Output Capacitance	$I_E = 0; V_{CB} = -10\text{V}; f_{test} = 1\text{MHz}$		90		pF

## Switching Times

$t_{on}$	Turn-on Time	$I_C = -2\text{A}; R_L = 10\Omega,$ $I_{B1} = -I_{B2} = -0.2\text{A}, V_{CC} = -20\text{V}$		0.25		$\mu\text{s}$
$t_{stg}$	Storage Time			0.75		$\mu\text{s}$
$t_f$	Fall Time			0.25		$\mu\text{s}$